

IN THE CLAIMS:

Please amend the claims as follows:

1-52. (Cancelled)

53. (Original) A semiconductor thin film formed on an insulating base, comprising: micro-projections formed on the surface of said semiconductor thin film.

54. (Original) A semiconductor thin film according to claim 53, wherein said micro-projections are arranged in an approximately regular pattern.

55. (Original) A semiconductor thin film according to claim 53, wherein a height of each of said micro-projections is in a range of 20 nm or less.

56. (Original) A semiconductor thin film according to claim 53, wherein a diameter of each of said micro-projections is in a range of 0.1 μ m or less.

57. (Original) A semiconductor thin film according to claim 53, wherein a radius of curvature of each of said micro-projections is in a range of 60 nm or more.

58. (Original) A semiconductor thin film according to claim 53, wherein a density of said micro-projections is in a range of 1×10^{10} pieces/cm² or less.

59. (Original) A semiconductor thin film according to claim 53, wherein a thickness of said semiconductor thin film is in a range of 50 nm or less.

60. (Original) A semiconductor thin film according to claim 53, wherein said micro-projections are formed by uplift of boundary portions among polycrystalline grains in said semiconductor thin film.

61. (Original) A semiconductor thin film according to claim 53, wherein said semiconductor thin film is made of non-single crystals, single crystals, or a combination thereof.

62. (Original) A semiconductor thin film according to claim 53, wherein said semiconductor thin film contains a single crystal region having a size of $1 \times 10^{-8} \text{ cm}^2$ or more.

63. (Original) A semiconductor thin film according to claim 53, wherein said semiconductor thin film contains a single crystal region having an orientation plane which is either of the (100), (111), and (110) planes.53.

64-125. (Cancelled)

126. (Original) A semiconductor thin film comprising: an insulating base; and a polycrystalline thin film formed in said insulating base, in which polycrystalline grains are aligned in an approximately regular pattern;
wherein micro-projections are each formed at a boundary position among at least three or more of said polycrystalline grains.

127. (Original) A semiconductor thin film according to claim 126, wherein said micro-projections are aligned in an approximately regular pattern.

28. (Original) A semiconductor thin film according to claim 126, wherein a thickness of said semiconductor thin film is in a range of 50 nm or less.

129. (Original) A semiconductor thin film according to claim 126, wherein a size of each of said polycrystalline grains is in a range of 0.1 μm to 4.0 μm .

130-181. (Cancelled)